

Docket No.: 004192.P053D

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application for:

Min-hwa Chi

Application No.: 09/865,929

Filed: May 24, 2001

For: TRANSISTOR AND LOGIC CIRCUIT ON
THIN SILICON-ON-INSULATOR WAFERS
BASED ON GATE INDUCED DRAIN
LEAKAGE CURRENTS

Examiner: Kang, Donghee

Art Group: 2811

Mail Stop: Issue Fee (Drawings)
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

TRANSMITTAL OF FORMAL DRAWINGS

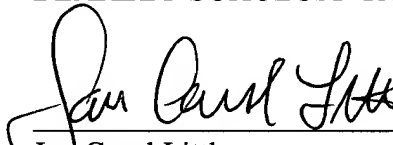
Dear Sir/Madam:

Enclosed herewith for filing in the above-identified U.S. patent application are the formal drawings, Figures 1-12 (9 sheets).

Respectfully submitted,

BLAKELY SOKOLOFF TAYLOR & ZAFMAN, LLP

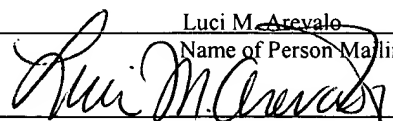
Date: 8/12/03


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on August 12, 2003
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